

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

MCH6605 — General-Purpose Switching Device Applications

Features

- · Low ON-resistance
- · Ultrahigh-speed switching
- · 4V drive
- · Composite type with 2 MOSFETs contained in a single package, facilitating high-density mounting

Specifications

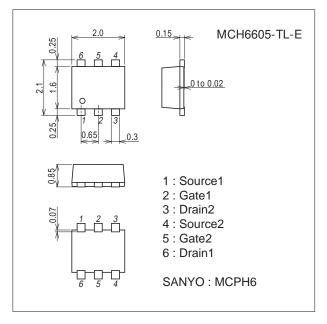
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-50	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		-0.14	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-0.56	Α
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm ² ×0.8mm)1unit	0.8	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

This product is designed to "ESD immunity $< 200V^*$ ", so please take care when handling.

Package Dimensions

unit : mm (typ) 7022A-006



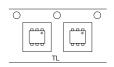
Product & Package Information

• Package : MCPH6

• JEITA, JEDEC : SC-88, SC-70-6, SOT-363

• Minimum Packing Quantity : 3,000 pcs./reel

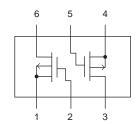
Packing Type: TL



Marking



Electrical Connection



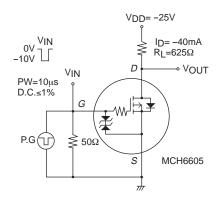
^{*} Machine Model

MCH6605

Electrical Characteristics at Ta=25°C

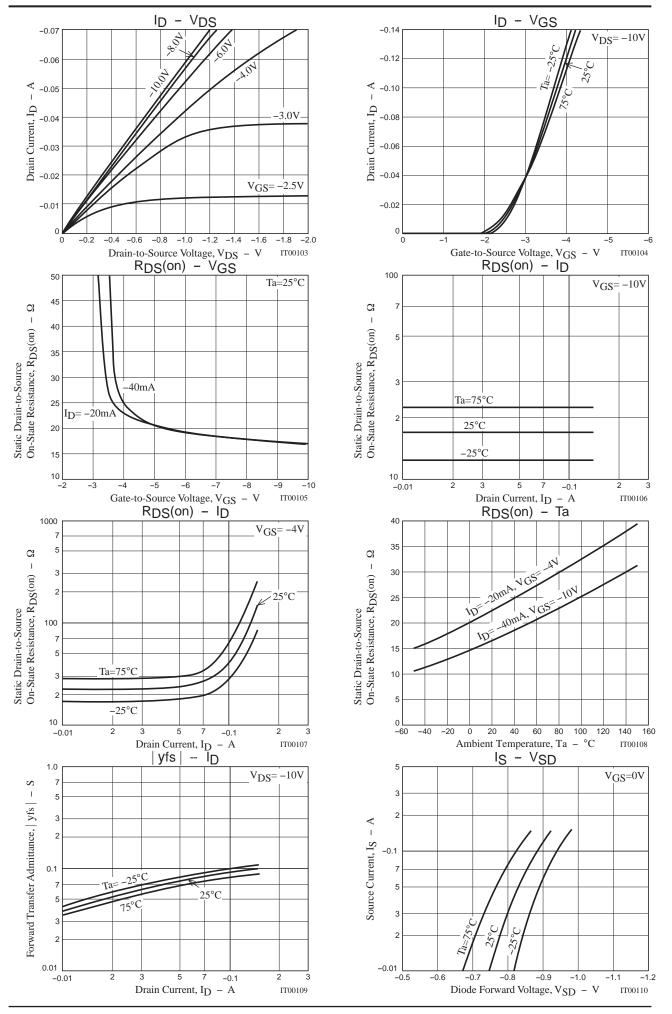
Parameter	Symbol	Conditions	Ratings			Unit	
Farameter	Syllibol	Conditions	min	typ	max	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	-50			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-50V, V _{GS} =0V			-1	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	V _{GS} (off)	V _{DS} =-10V, I _D =-100μA	-1		-2.5	V	
Forward Transfer Admittance	yfs	V _{DS} =-10V, I _D =-40mA	50	70		mS	
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =-40mA, V _G S=-10V		17	22	Ω	
	R _{DS} (on)2	I _D =-20mA, V _G S=-4V		23	32	Ω	
Input Capacitance	Ciss			6.2		pF	
Output Capacitance	Coss	V _{DS} =-10V, f=1MHz		4.0		pF	
Reverse Transfer Capacitance	Crss			1.3		pF	
Turn-ON Delay Time	t _d (on)			13		ns	
Rise Time	t _r	See appointed Test Circuit		10		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		100		ns	
Fall Time	tf			150		ns	
Total Gate Charge	Qg			1.32		nC	
Gate-to-Source Charge	Qgs	V _{DS} =-10V, V _{GS} =-10V, I _D =-70mA		0.17		nC	
Gate-to-Drain "Miller" Charge	Qgd			0.34		nC	
Diode Forward Voltage	VSD	IS=-70mA, VGS=0V		-0.85	-1.2	V	

Switching Time Test Circuit

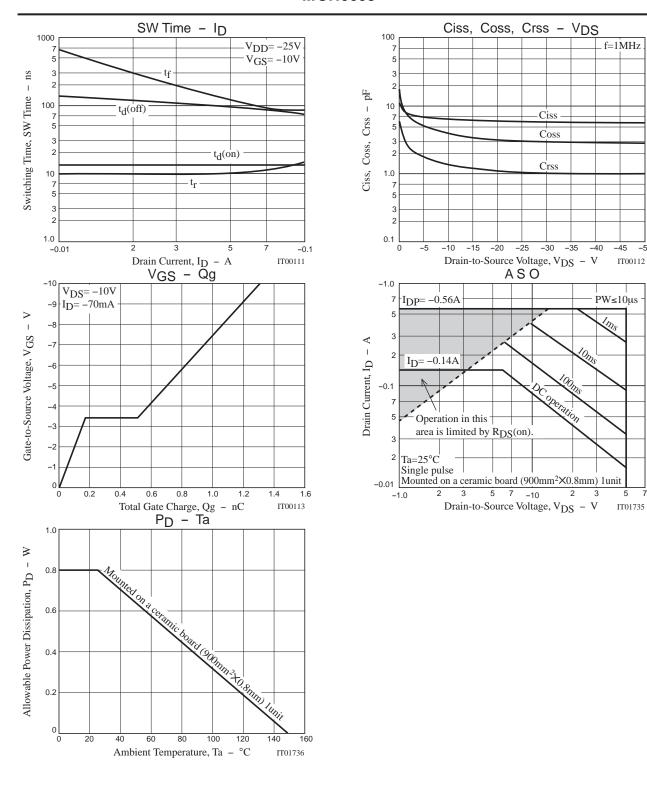


Ordering Information

Device			memo
MCH6605-TL-E	MCPH6	3,000pcs./reel	Pb Free



MCH6605

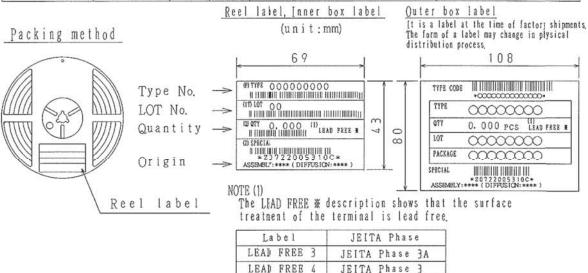


Taping Specification

MCH6605-TL-E

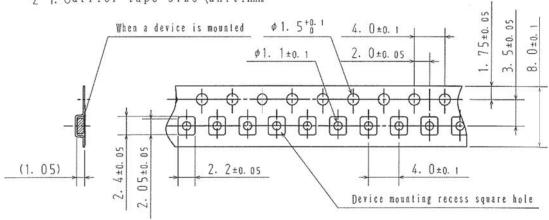
1. Packing Format

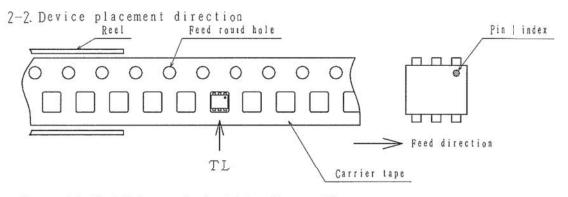
Package Name Carrier Tape Type	Maximum Number of devices contained (yes)			Packing format		
	Туре	Reel	[nner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
МСРН6	MCP4	3, 000	15, 000	90, 000		6 inner boxes contained Dimensions:mm (external) 440×195×210



2. Taping configuration





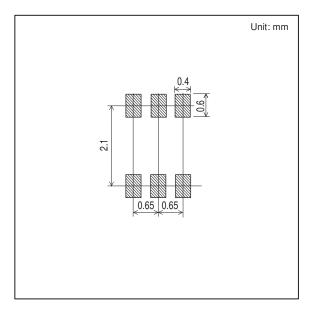


Those with pin 1 index on the feed hole side ·····TL

Outline Drawing

MCH6605-TL-E

Land Pattern Example



Note on usage: Since the MCH6605 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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